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DS90LV004 4-Channel LVDS Buffer/Repeater with Pre-Emphasis

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DS90LV004 4-Channel LVDS Buffer/Repeater with Pre-Emphasis

General Description

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The DS90LV004 is a four channel 1.5 Gbps LVDS buffer/ repeater. High speed data paths and flow-through pinout minimize internal device jitter and simplify board layout, while configurable pre-emphasis overcomes ISI jitter effects from lossy backplanes and cables. The differential inputs interface to LVDS, and Bus LVDS signals such as those on National's 10-, 16-, and 18- bit Bus LVDS SerDes, as well as CML and LVPECL. The differential inputs and outputs are internally terminated with a 100 Ω resistor to improve performance and minimize board space. The repeater function is especially useful for boosting signals for longer distance transmission over lossy cables and backplanes.

Features

- 1.5 Gbps data rate per channel
- Configurable pre-emphasis drives lossy backplanes and cables
- Low output skew and jitter
- Hot plug protection
- LVDS/CML/LVPECL compatible input, LVDS output
- On-chip 100Ω input and output termination
- 15 kV ESD protection on LVDS inputs and outputs
- Single 3.3V supply
- Very low power consumption
- Industrial -40 to +85°C temperature range
- Small TQFP Package Footprint
- Evaluation Kit Available
- See SCAN90004 for JTAG-enabled version



Block and Connection Diagrams

DS90LV004

Pin Descriptions

Pin	TQFP Pin	I/O. Type	Description						
Name	Number								
DIFFERENTIAL INPUTS									
IN0+	13	I, LVDS	Channel 0 inverting and non-inverting differential inputs.						
IN0-	14								
IN1+	15	I, LVDS	Channel 1 inverting and non-inverting differential inputs.						
IN1-	16								
IN2+	19	I, LVDS	Channel 2 inverting and non-inverting differential inputs.						
IN2-	20								
IN3+	21	I, LVDS	Channel 3 inverting and non-inverting differential inputs.						
IN3-	22								
DIFFERENTIAL OUTPUTS									
OUT0+	48	O, LVDS	Channel 0 inverting and non-inverting differential outputs. (Note 1)						
OUT0-	47								
OUT1+	46	O, LVDS	Channel 1 inverting and non-inverting differential outputs. (Note 1)						
OUT1-	45								
OUT2+	42	O, LVDS	Channel 2 inverting and non-inverting differential outputs. (Note 1)						
OUT2-	41								
OUT3+	40	O, LVDS	Channel 3 inverting and non-inverting differential outputs. (Note 1)						
OUT3-	39								
DIGITAL	CONTROL INTER	FACE							
PWDN	12	I, LVTTL	A logic low at PWDN activates the hardware power down mode.						
PEM0	1	I, LVTTL	Pre-emphasis Control Inputs (affects all Channels)						
PEM1	2								
POWER									
V _{DD}	3, 4, 5, 7, 10, 11,	I, Power	$V_{DD} = 3.3V, \pm 5\%$						
	27, 28, 29, 32,								
	33, 34								
GND	8, 9, 17, 18, 23,	I, Power	Ground						
	24, 25, 26, 37,								
	38, 43, 44								
N/C	6, 30, 31, 35, 36		No Connect						

Note 1: The LVDS outputs do not support a multidrop (BLVDS) environment. The LVDS output characteristics of the DS90LV004 device have been optimized for point-to-point backplane and cable applications.

Absolute Maximum Ratings (Note 2)

Supply Voltage (V _{DD})	-0.3V to +4.0V
CMOS Input Voltage	–0.3V to (V _{DD} +0.3V)
LVDS Receiver Input Voltage	-0.3V to (V _{DD} +0.3V)
LVDS Driver Output Voltage	–0.3V to (V _{DD} +0.3V)
LVDS Output Short Circuit Current	+40 mA
Junction Temperature	+150°C
Storage Temperature	–65°C to +150°C
Lead Temperature (Solder, 4sec)	260°C
Max Pkg Power Capacity @ 25°C	1.64W
Thermal Resistance (θ_{JA})	76°C/W
Package Derating above +25°C	13.2mW/°C
ESD Last Passing Voltage	
HBM, 1.5kΩ, 100pF	15 kV

EIAJ, 0Ω, 200pF

250V

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Recommended Operating Conditions

Supply Voltage (V _{CC})	3.15V to 3.45V
Input Voltage (V _I) (Note 3)	0V to V_{CC}
Output Voltage (V _O)	0V to $V_{\rm CC}$
Operating Temperature (T _A)	
Industrial	-40°C to +85°C

Note 2: Absolute maximum ratings are those values beyond which damage to the device may occur. The databook specifications should be met, without exception, to ensure that the system design is reliable over its power supply, temperature, and output/input loading variables. National does not recommend operation of products outside of recommended operation conditions. **Note 3:** V_{ID} max < 2.4V

Electrical Characteristics

Over recommended operating supply and temperature ranges unless other specified.

Symbol	Parameter	Conditions	Min	Typ (Note 4)	Мах	Units		
LVTTL DC SPECIFICATIONS (PWDN, PEM0, PEM1)								
V _{IH}	High Level Input Voltage		2.0		V_{DD}	V		
V _{IL}	Low Level Input Voltage		GND		0.8	V		
I _{IH}	High Level Input Current	$V_{IN} = V_{DD} = V_{DDMAX}$	-10		+10	μA		
IIL	Low Level Input Current	$V_{IN} = V_{SS}, V_{DD} = V_{DDMAX}$	-10		+10	μA		
C _{IN1}	Input Capacitance	Any Digital Input Pin to V _{SS}		3.5		pF		
V _{CL}	Input Clamp Voltage	$I_{CL} = -18 \text{ mA}$	-1.5	-0.8		V		
LVDS INPUT DC SPECIFICATIONS (INn±)								
V _{TH}	Differential Input High	$V_{CM} = 0.8V$ to 3.4V,		0	100	m\/		
	Threshold (Note 5)	V _{DD} = 3.45V		0	100	IIIV		
V_{TL}	Differential Input Low	$V_{CM} = 0.8V$ to 3.4V,	_100	0		mV		
	Threshold (Note 5)	V _{DD} = 3.45V	-100	0		IIIV		
V _{ID}	Differential Input Voltage	$V_{CM} = 0.8V$ to 3.4V, $V_{DD} = 3.45V$	100		2400	mV		
V _{CMR}	Common Mode Voltage Range	V _{ID} = 150 mV, V _{DD} = 3.45V	0.05		3.40	V		
C _{IN2}	Input Capacitance	IN+ or IN– to V _{SS}		3.5		pF		
I _{IN}	Input Current	$V_{IN} = 3.45V, V_{DD} = V_{DDMAX}$	-10		+10	μA		
		$V_{IN} = 0V, V_{DD} = V_{DDMAX}$	-10		+10	μA		

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Electrical Characteristics (Continued) Over recommended operating supply and temperature ranges unless other specified. Тур Conditions Min Units Symbol Parameter Max (Note 4) LVDS OUTPUT DC SPECIFICATIONS (OUTn±) Vod Differential Output Voltage, $R_1 = 100\Omega$ external resistor between OUT+ and 250 500 600 mV OUT-0% Pre-emphasis (Note 5) ΔV_{OD} Change in V_{OD} between -35 35 mV **Complementary States** V_{OS} Offset Voltage (Note 6) 1.05 1.18 1.475 V Change in Vos between ΔV_{OS} -35 35 mV **Complementary States** Output Short Circuit Current OUT+ or OUT- Short to GND -60 -90 los mΑ OUT+ or OUT- to GND when TRI-STATE pF C_{OUT2} **Output Capacitance** 5.5 SUPPLY CURRENT (Static) I_{CC} Supply Current All inputs and outputs enabled and active, terminated with differential load of 100Ω 117 140 mΑ between OUT+ and OUT-. $\overline{PWDN} = L$ I_{CCZ} Supply Current - Power Down 2.7 6 mΑ Mode SWITCHING CHARACTERISTICS-LVDS OUTPUTS Differential Low to High Use an alternating 1 and 0 pattern at 200 Mbps, t_{LHT} 210 300 ps **Transition Time** measure between 20% and 80% of $V_{\rm OD}$. Differential High to Low t_{HLT} 210 300 ps **Transition Time** Use an alternating 1 and 0 pattern at 200 Mbps, t_{PLHD} Differential Low to High 2.0 3.2 ns Propagation Delay measure at 50% $V_{\rm OD}$ between input to output. Differential High to Low t_{PHLD} 2.0 3.2 ns **Propagation Delay** Pulse Skew It_{PLHD}-t_{PHLD} 25 80 ps t_{SKD1} Difference in propagation delay (t_{PLHD} or t_{PHLD}) Output Channel to Channel t_{skcc} 125 50 ps Skew among all output channels. RJ - Alternating 1 and 0 at 750 MHz (Note 8) Jitter (0% Pre-emphasis) 1.1 1.5 psrms t_{JIT} (Note 7) DJ - K28.5 Pattern, 1.5 Gbps (Note 9) 43 62 psp-p TJ - PRBS 2²³-1 Pattern, 1.5 Gbps (Note 10) 35 85 psp-p Time from PWDN to OUT± change from LVDS Output Enable Time t_{on} 300 ns TRI-STATE to active. Time from PWDN to OUT± change from active LVDS Output Disable Time toFF 12 ns to TRI-STATE.

Note 4: Typical parameters are measured at $V_{DD} = 3.3V$, $T_A = 25$ °C. They are for reference purposes, and are not production-tested.

Note 5: Differential output voltage V_{DD} is defined as ABS(OUT+-OUT-). Differential input voltage V_{ID} is defined as ABS(IN+-IN-).

Note 6: Output offset voltage V_{OS} is defined as the average of the LVDS single-ended output voltages at logic high and logic low states.

Note 7: Jitter is not production tested, but guaranteed through characterization on a sample basis.

Note 8: Random Jitter, or RJ, is measured RMS with a histogram including 1500 histogram window hits. The input voltage = V_{ID} = 500mV, 50% duty cycle at 750MHz, $t_r = t_f = 50$ ps (20% to 80%).

Note 9: Deterministic Jitter, or DJ, is measured to a histogram mean with a sample size of 350 hits. The input voltage = V_{ID} = 500mV, K28.5 pattern at 1.5 Gbps, $t_r = t_f = 50ps$ (20% to 80%). The K28.5 pattern is repeating bit streams of (0011111010 110000101).

Note 10: Total Jitter, or TJ, is measured peak to peak with a histogram including 3500 window hits. Stimulus and fixture Jitter has been subtracted. The input voltage = V_{ID} = 500mV, 2²³-1 PRBS pattern at 1.5 Gbps, $t_r = t_f = 50$ ps (20% to 80%).

Feature Descriptions

INTERNAL TERMINATIONS

The DS90LV004 has integrated termination resistors on both the input and outputs. The inputs have a 100 Ω resistor across the differential pair, placing the receiver termination as close as possible to the input stage of the device. The LVDS outputs also contain an integrated 100 Ω ohm termination resistor, this resistor is used to reduce the effects of Near End Crosstalk (NEXT) and does not take the place of the 100 ohm termination at the inputs to the receiving device. The integrated terminations improve signal integrity and decrease the external component count resulting in space savings.

OUTPUT CHARACTERISTICS

The output characteristics of the DS90LV004 have been optimized for point-to-point backplane and cable applications, and are not intended for multipoint or multidrop signaling.

POWERDOWN MODE

The PWDN input activates a hardware powerdown mode. When the powerdown mode is active (PWDN=L), all input and output buffers and internal bias circuitry are powered off and disabled. Outputs are tri-stated in powerdown mode. When exiting powerdown mode, there is a delay associated with turning on bandgap references and input/output buffer circuits as indicated in the LVDS Output Switching Characteristics

PRE-EMPHASIS

Pre-emphasis dramatically reduces ISI jitter from long or lossy transmission media. Two pins are used to select the pre-emphasis level for all outputs: off, low, medium, or high.

Pre-emphasis Control Selection Table

PEM1	PEM0	Pre-Emphasis
0	0	Off
0	1	Low
1	0	Medium
1	1	High

INPUT FAILSAFE BIASING

External pull up and pull down resistors may be used to provide enough of an offset to enable an input failsafe under open-circuit conditions. This configuration ties the positive LVDS input pin to V_{DD} thru a pull up resistor and the negative LVDS input pin is tied to GND by a pull down resistor. The pull up and pull down resistors should be in the 5k Ω to 15k Ω range to minimize loading and waveform distortion to the driver. The common-mode bias point ideally should be set to approximately 1.2V (less than 1.75V) to be compatible with the internal circuitry. Please refer to application note AN-1194 "Failsafe Biasing of LVDS Interfaces" for more information.

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Typical Performance Characteristics

Power Supply Current vs. Bit Data Rate



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Dynamic power supply current was measured while running a clock or PRBS 2²³-1 pattern with all 4 channels active. V_{CC} = 3.3V, T_A = +25°C, V_{ID} = 0.5V, V_{CM} = 1.2V



TEMPERATURE (°C)

Total Jitter (T_J) vs. Bit Data Rate



Total Jitter measured at 0V differential while running a PRBS 2²³-1 pattern with a single channel active. V_{CC} = 3.3V, T_A = +25°C, V_{ID} = 0.5V, 0% Pre-emphasis

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Positive Edge Transition vs. Pre-emphasis Level



Total Jitter measured at 0V differential while running a PRBS 2^{23} -1 pattern with a single channel active. V_{CC} = 3.3V, V_{ID} = 0.5V, V_{CM} = 1.2V, 1.5 Gbps data rate, 0% Pre-emphasis

FIGURE 1. Typical Performance Characteristics of the DS90LV004



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